Supplementary Information (SI) for Nanoscale.
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Nanoscale

Supporting Information

Title:

Influence of TiN diffusion barrier on the leakage current and ferroelectricity in Al-doped HfO_x ferroelectric memristor and its application to neuromorphic computing

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Supplementary figures

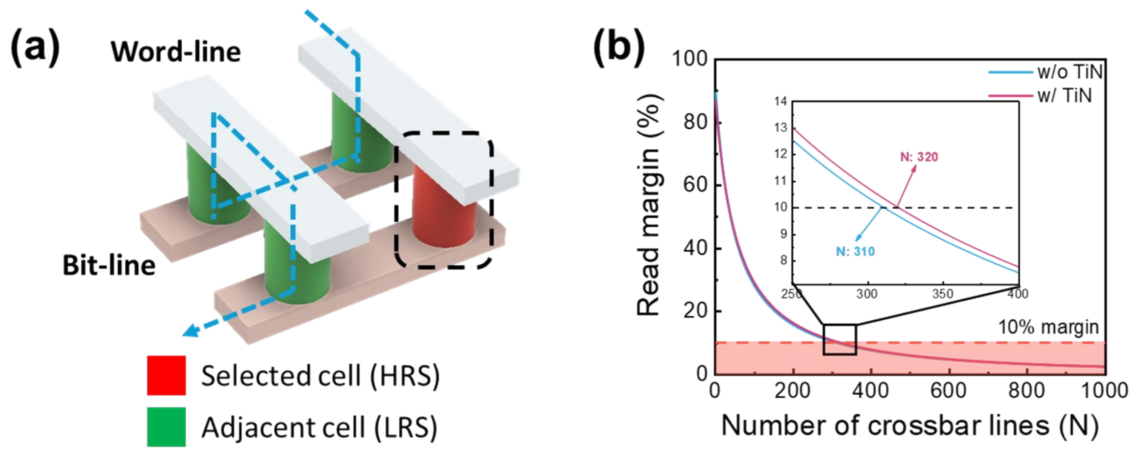

Figure S1. (a) Schematic of worst case in the array structure. (b) Estimation of the crossbar array read margin with application of the V/2 scheme.

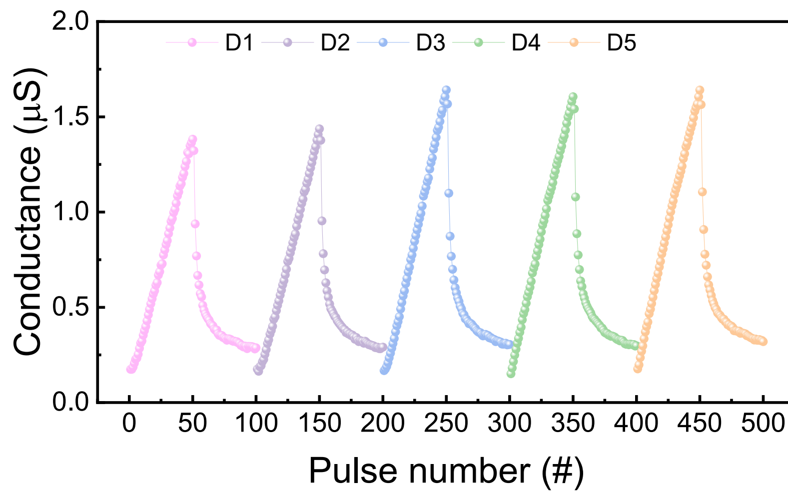

Figure S2. The conductance change of potentiation and depression of different five d evices.